



ZHEJIANG UNIÜ-NE Technology CO., LTD

浙江宇力微新能源科技有限公司



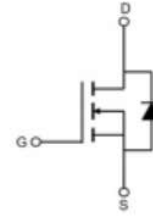
AP3010 Data Sheet

V 1.1

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Feature

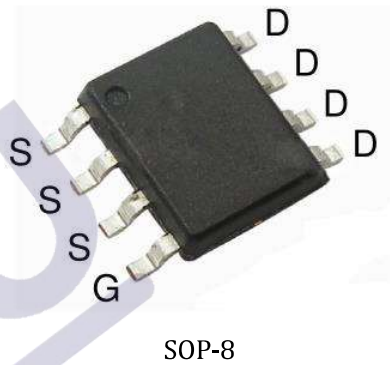
- 30V,10A
 $R_{DS(ON)} < 10m\Omega @ V_{GS}=10V$ TYP:8.5m Ω
 $R_{DS(ON)} < 14m\Omega @ V_{GS}=4.5V$ TYP:11 m Ω
- Advanced Trench Technology
- Lead free product is acquired
- Excellent $R_{DS(ON)}$ and Low Gate Charge



Schematic Diagram

Application

- PWM applications
- Load Switch
- Power management



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity (PCS)
3010	AP3010	SOP-8	13 inch	-	4000

ABSOLUTE MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current (T _a =25°C)	I _D	10	A
Continuous Drain Current (T _a =100°C)	I _D	6	A
Pulsed Drain Current ⁽¹⁾	I _{DM}	50	A
Singel Pulsed Avalanche Energy ⁽²⁾	E _{AS}	45	mJ
Power Dissipation	P _D	2.5	W
Thermal Resistance from Junction to Case ⁽⁴⁾	R _{θJC}	50	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55~ +150	°C

MOSFET ELECTRICAL CHARACTERISTICS($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	30	-	-	V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 30V, V_{GS} = 0V$	-	-	1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	± 100	nA
Gate threshold voltage ⁽³⁾	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1	1.6	2.5	V
Drain-source on-resistance ⁽³⁾	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 10A$	-	8.5	10	m Ω
		$V_{GS} = 4.5V, I_D = 5A$	-	11	14	
Dynamic characteristics						
Input Capacitance	C_{iss}	$V_{DS} = 15V, V_{GS} = 0V, f = 1MHz$	-	900	-	pF
Output Capacitance	C_{oss}		-	140	-	
Reverse Transfer Capacitance	C_{rss}		-	120	-	
Switching characteristics						
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 15V, I_D = 10A, R_L = 6\Omega$ $V_{GS} = 10V, R_G = 1\Omega$	-	6	-	ns
Turn-on rise time	t_r		-	5	-	
Turn-off delay time	$t_{d(off)}$		-	25	-	
Turn-off fall time	t_f		-	7	-	
Total Gate Charge	Q_g	$V_{DS} = 15V, I_D = 10A,$ $V_{GS} = 10V$	-	19	-	nC
Gate-Source Charge	Q_{gs}		-	6.3	-	
Gate-Drain Charge	Q_{gd}		-	4.5	-	
Source-Drain Diode characteristics						
Diode Forward voltage ⁽³⁾	V_{DS}	$V_{GS} = 0V, I_S = 10A$	-	-	1.2	V
Diode Forward current ⁽⁴⁾	I_S		-	-	10	A

Notes:

1. Repetitive Rating: pulse width limited by maximum junction temperature
2. EAS Condition: $T_J = 25^\circ\text{C}, V_{DD} = 15V, R_G = 25\Omega, L = 0.5mH$
3. Pulse Test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
4. Surface Mounted on FR4 Board, $t \leq 10$ sec

Test Circuit

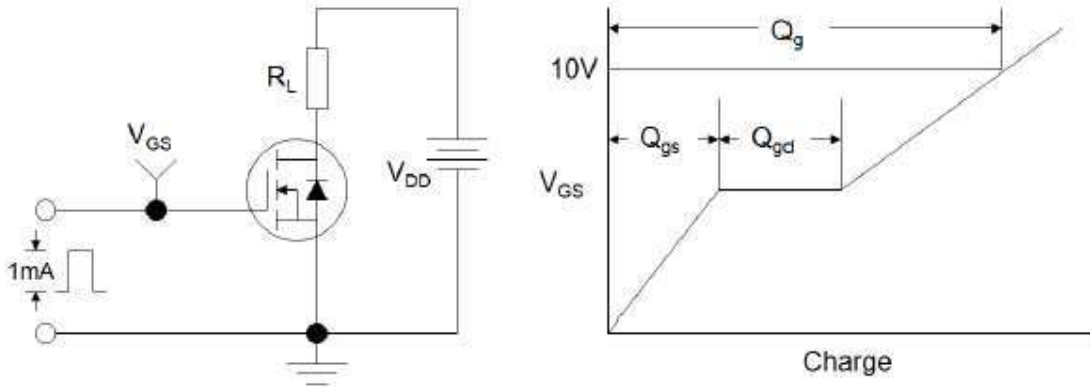


Figure1:Gate Charge Test Circuit & Waveform

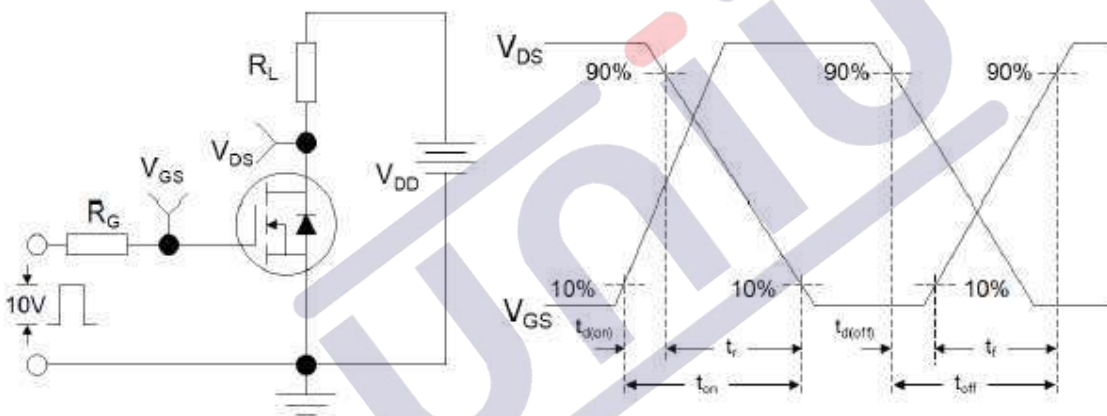


Figure 2: Resistive Switching Test Circuit & Waveforms

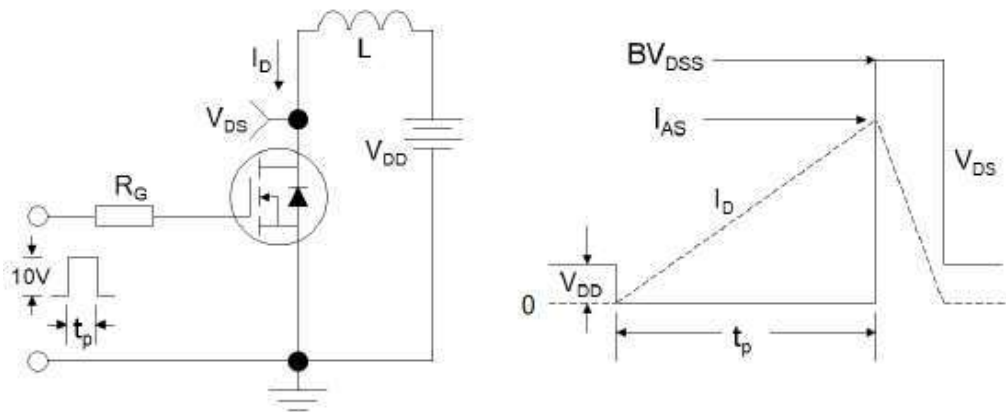


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

Typical Performance Characteristics

Figure 1: Output Characteristics

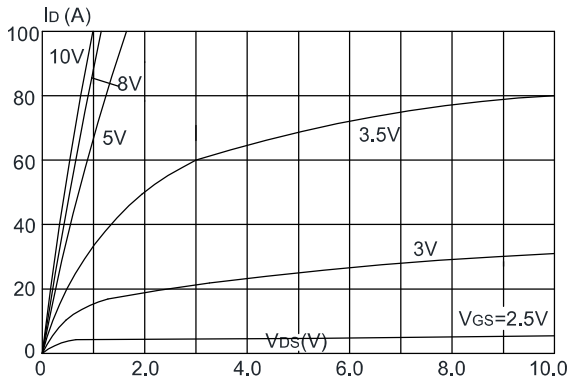


Figure 2: Typical Transfer Characteristics

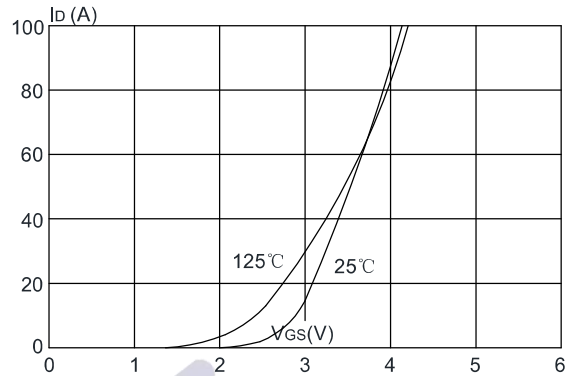


Figure 3: On-resistance vs. Drain Current

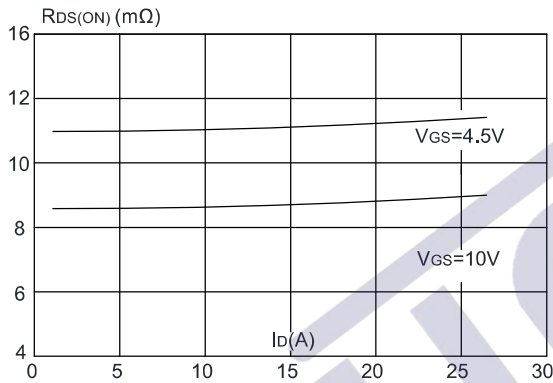


Figure 4: Body Diode Characteristics

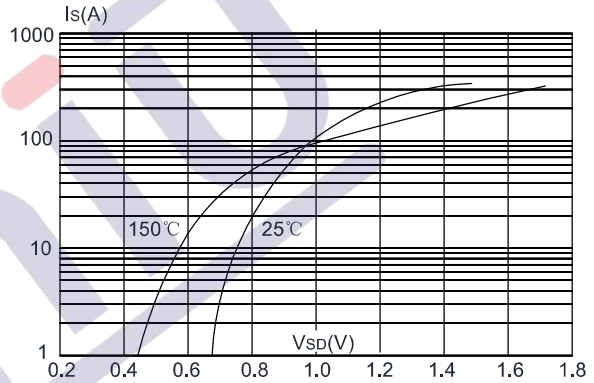


Figure 5: Gate Charge Characteristics

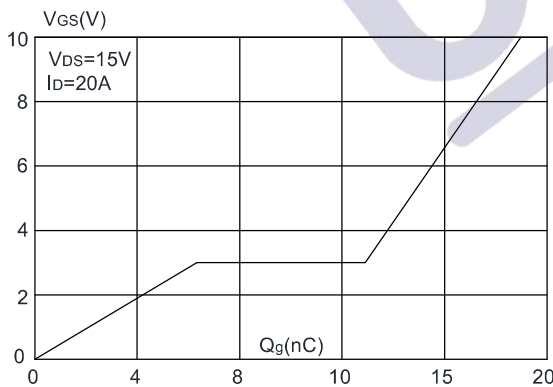


Figure 6: Capacitance Characteristics

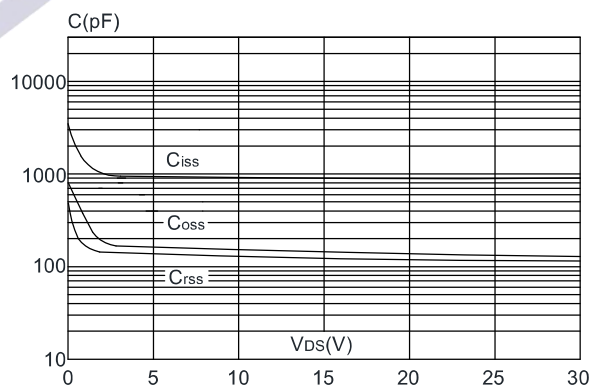


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

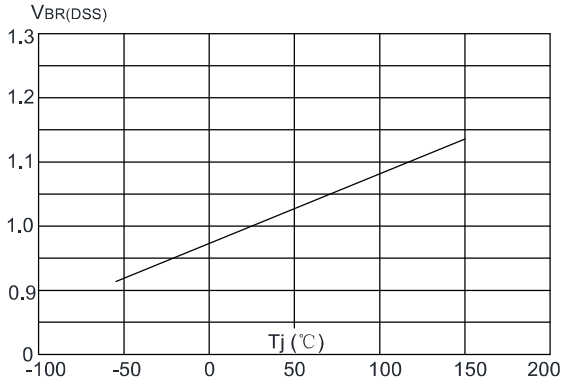


Figure 8: Normalized on Resistance vs. Junction Temperature

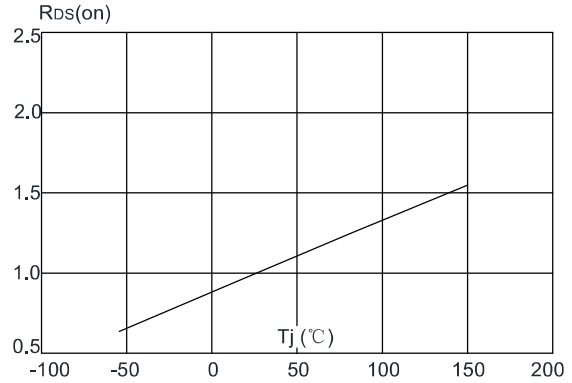


Figure 9: Maximum Safe Operating Area

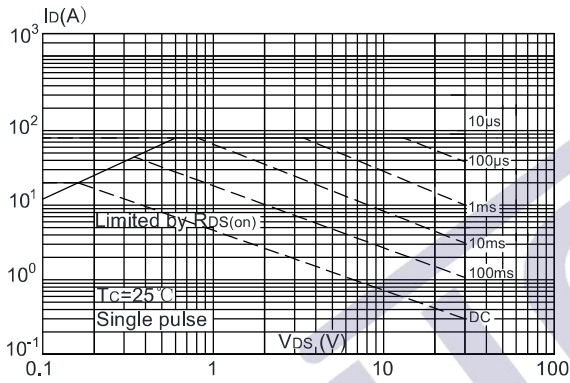


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

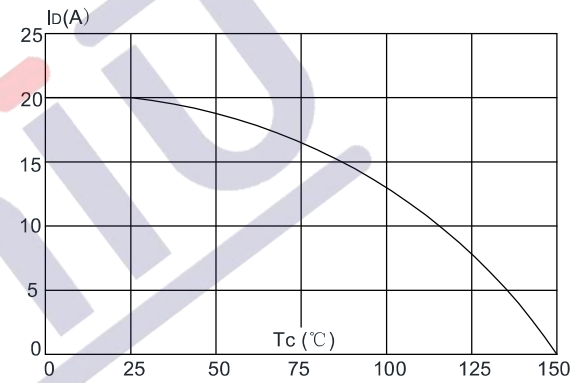
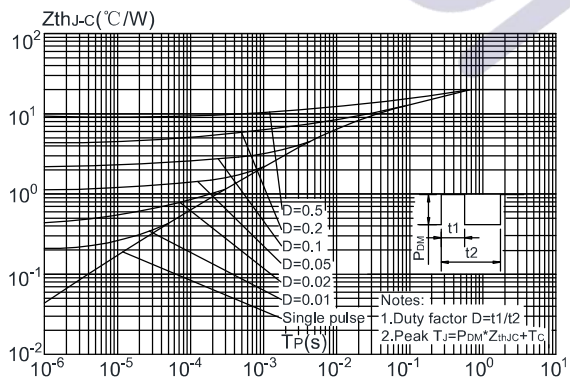
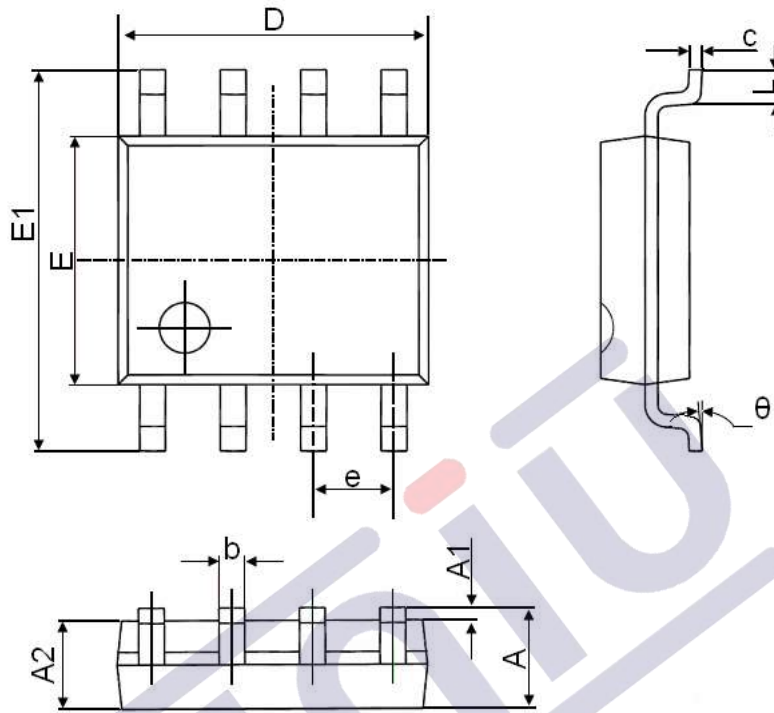


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

1.版本记录

DATE	REV.	DESCRIPTION
2018/04/16	1.0	First Release
2021/11/10	1.1	Layout adjustment

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3.联系我们

浙江宇力微新能源科技有限公司

总部地址：绍兴市越城区斗门街道袍渎路25号中节能科创园45幢4/5楼

电话：0575-85087896（研发部）

传真：0575-88125157

E-mail: htw@uni-semic.com

无锡地址：无锡市锡山区先锋中路6号中国电子（无锡）数字芯城1#综合楼503室

电话：0510-85297939

E-mail: zh@uni-semic.com

深圳地址：深圳市宝安区西乡街道南昌社区宝源路泳辉国际商务大厦410

电话：0755-84510976

E-mail: htw@uni-semic.com